











LF347, LF347B

SLOS013C -MARCH 1987-REVISED MARCH 2016

LF347, LF347B JFET-Input Quad Operational Amplifiers

Features

Low Input Bias Current: 50 pA Typical

Low Input Noise Current: 0.01 pA/\(\sqrt{Hz}\) Typical

Low Total Harmonic Distortion

Low Supply Current: 8 mA Typical

Gain Bandwidth: 3 MHz Typical

High Slew Rate: 13 V/ms Typical

Applications

Motor Integrated Systems: UPS

Drives and Control Solutions: AC Inverters and VF

Renewables: Solar Inverters

Pro Audio Mixers

Oscilloscopes

3 Description

The LF347 and LF347B devices are low-cost, highspeed, JFET-input operational amplifiers. They require low supply current yet maintain a large gainbandwidth product and a fast slew rate. In addition, their matched high-voltage JFET inputs provide very low input bias and offset current.

The LF347 and LF347B can be used in applications such as high-speed integrators, digital-to-analog converters, sample-and-hold circuits, and many other circuits.

The LF347 and LF347B devices are characterized for operation from 0°C to 70°C.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
LF347D, LF347BD	SOIC (14)	8.65 mm × 3.91 mm
LF347N, LF347BN	PDIP (14)	19.30 mm × 6.35 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Symbol (Each Amplifier)

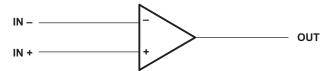




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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

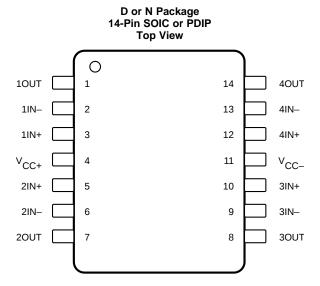
Changes from Revision B (August 1994) to Revision C

Page

Added ESD Ratings table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and



5 Pin Configuration and Functions



Pin Functions

	PIN	1/0	DESCRIPTION
NO.	NAME	I/O	DESCRIPTION
1	1OUT	0	Output pin of amplifier 1
2	1IN-	I	Inverting input pin of amplifier 1
3	1IN+	1	Noninverting input pin of amplifier 1
4	V _{CC+}	_	Positive Supply
5	2IN+	1	Noninverting input pin of amplifier 2
6	2IN-	1	Inverting input pin of amplifier 2
7	2OUT	0	Output pin of amplifier 2
8	3OUT	0	Output pin of amplifier 3
9	3IN-	1	Inverting input pin of amplifier 3
10	3IN+	I	Noninverting input pin of amplifier 3
11	V _{CC} -	_	Negative Supply
12	4IN+	1	Noninverting input pin of amplifier 4
13	4IN-	I	Inverting input pin of amplifier 4
14	4OUT	0	Output pin of amplifier 4



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{CC+}	Supply voltage		18	V
V _{CC} -	Supply voltage		-18	V
V_{ID}	Differential input voltage	-30	30	V
VI	Input voltage (2)	-15	15	V
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds		260	°C
TJ	Operating virtual junction temperature		150	°C
T _{stg}	Storage temperature	-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	V
V(E	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1000	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
T _A	free-air temperature	0	70	°C
V _{CC+}	Supply voltage	3.5	18	V
V _{CC} -	Supply voltage	-3.5	-18	V
V_{CM}	Common-mode voltage	V _{CC-} + 4	$V_{CC+}-4$	V
T _A	Operating temperature	0	70	°C

6.4 Thermal Information

		LF347,		
	THERMAL METRIC ⁽¹⁾	D (SOIC)	N (PDIP)	UNIT
		14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	74.4	42.7	°C/W
R ₀ JC(top)	Junction-to-case (top) thermal resistance	32.5	29.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	28.9	22.6	°C/W
ΨЈТ	Junction-to-top characterization parameter	3.7	13.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	28.6	22.5	°C/W

 For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

²⁾ Unless otherwise specified, the absolute maximum negative input voltage is equal to the negative power supply voltage.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics: LF347

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
	land offer the land	25°C			5	10	\/
V_{IO}	Input offset voltage	$V_{IC} = 0$, $R_S = 10 \text{ k}\Omega$	Full range ⁽¹⁾			13	mV
α_{VIO}	Average temperature coefficient of input offset voltage	$V_{IC} = 0$, $R_S = 10 \text{ k}\Omega$			18		μV/°C
	1	V 0	25°C		25	100	pA
I _{IO}	Input offset current ⁽²⁾	$V_{IC} = 0$	70°C			4	nA
I _{IB} Input bias current ⁽²⁾		25°C		50	200	pA	
I _{IB}	input bias current	$V_{IC} = 0$	70°C			8	nA
		Lower limit of range	-11	-12		.,	
V_{ICR}	Common-mode input voltage	Upper limit of range	11	15		V	
V _{OM}	Maximum peak output voltage swing	R _L = 10 kΩ		±12	±13.5		V
^	I ama airea I differential college	V .40.V D 01-0	25°C	25	100		\//\/
A_{VD}	Large signal differential voltage	$V_O = \pm 10 \text{ V}, R_L = 2 \text{ k}\Omega$	Full range	15			V/mV
ri	Input resistance	T _A = 25°C			10 ¹²		Ω
CMRR	Common-mode rejection ratio	$R_S \le 2 k\Omega$		70	100		dB
k _{SVR}	Supply-voltage rejection ratio	See ⁽³⁾		70	100		dB
I _{CC}	Supply current				8	11	mA

Full range is 0°C to 70°C.

6.6 Electrical Characteristics: LF347B

over operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CO	ONDITIONS	MIN	TYP	MAX	UNIT
V _{IO} Input offset voltage		$V_{IC} = 0, R_S = 10 \text{ k}\Omega$	25°C		3	5	mV
VIO	input onset voitage	$V_{IC} = 0, K_S = 10 \text{ K}\Omega$	Full range ⁽¹⁾			7	IIIV
α_{VIO}	Average temperature coefficient of input offset voltage	$V_{IC} = 0$, $R_S = 10 \text{ k}\Omega$			18		μV/°C
	Input offset current ⁽²⁾	V 0	25°C		25	100	pА
I _{IO}	input onset current—	V _{IC} = 0	70°C			4	nA
	L	V 0	25°C		50	200	рА
I _{IB}	Input bias current ⁽²⁾	V _{IC} = 0 70°C				8	nA
	O	Lower limit of range	-11	-12		V	
V _{ICR}	Common-mode input voltage	Upper limit of range	11	15		V	
V _{OM}	Maximum peak output voltage swing	R _L = 10 kΩ		±12	±13.5		V
^	l ann ainm al differential coltana	V .40 V D 01-0	25°C	50	100		\//\/
A _{VD}	Large signal differential voltage	$V_O = \pm 10 \text{ V}, R_L = 2 \text{ k}\Omega$	Full range	25			V/mV
r _i	Input resistance	T _{A = 25°C}	·		10 ¹²		Ω
CMRR	Common-mode rejection ratio	$R_{S \le 2 k\Omega}$		80	100		dB
k _{SVR}	Supply-voltage rejection ratio	See (3)			100		dB
I _{CC}	Supply current				8	11	mA

⁽¹⁾ Full range is 0°C to 70°C.

⁽²⁾ Input bias currents of a FET-input operational amplifier are normal junction reverse currents, which are temperature sensitive. Pulse techniques must be used that will maintain the junction temperatures as close to the ambient temperature as possible.

⁽³⁾ Supply-voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously.

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⁽³⁾ Supply-voltage rejection ratio is measured for both supply magnitudes increasing or decreasing simultaneously.

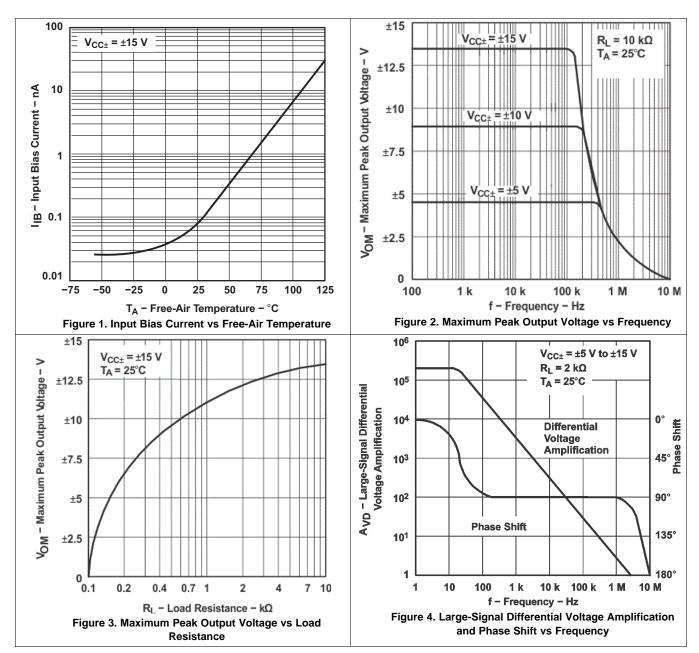


6.7 Switching Characteristics

 $V_{CC\pm} = \pm 15 \text{ V}, T_A = 25^{\circ}\text{C}$

	PARAMETER	TEST	CONDITIONS	MIN	TYP	MAX	UNIT
SR	Slew rate at unity gain	$V_I = 10 \text{ V},$ $C_L = 100 \text{ pF},$	$R_L = 2 k\Omega$, See Figure 5	8	13		V/µs
B ₁	Unity-gain bandwidth				3		MHz
V_{O1} / V_{O2}	Crosstalk attenuation	f = 1 kHZ			120		dB
V	Equivalent input noise	R _S = 20 Ω	f = 1 kHz		18		nV/√ Hz
V _n	voltage	$R_S = 20 \Omega$	f = 10 Hz to 10 kHz		4		μV
In	Equivalent input noise current	$R_S = 20 \Omega$,	f = 1 kHz		0.01		pA/√ Hz

6.8 Typical Characteristics



Product Folder Links: LF347 LF347B

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7 Parameter Measurement Information

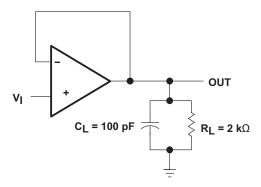


Figure 5. Unity-Gain Amplifier

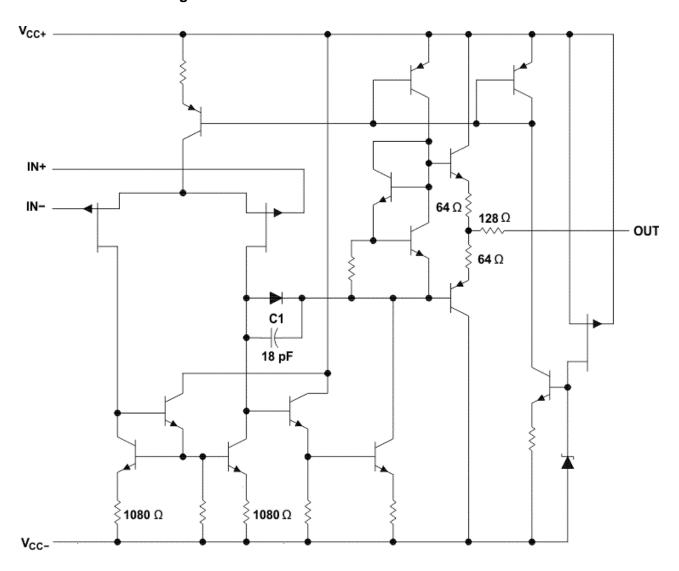


8 Detailed Description

8.1 Overview

The LF347 is a JFET-input operational amplifier with low input bias and offset currents and fast slew rate. Each amplifier features JFET inputs (for high input impedance) coupled with bipolar output stages integrated on a single monolithic chip. The output is protected against shorts due to the resistive $200-\Omega$ output impedance.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Slew Rate

The slew rate is the rate at which an operational amplifier can change its output when there is a change on the input. These devices have a 13-V/µs slew rate.

8.4 Device Functional Modes

These devices are powered on when the supply is connected. This device can be operated as a single-supply operational amplifier or dual-supply amplifier depending on the application.

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9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LF347 has four independent amplifiers that have very low input bias current which allow using higher resistance resistors in the feedback network. The upper input common mode range typically goes to the positive supply rail. The lower common mode range does not include the negative supply rail; it must be at least 4-V greater. Output resistance is $200~\Omega$ to protect the device from accidental shorts.

9.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier. This amplifier takes a positive voltage on the input, and makes it a negative voltage of the same magnitude. In the same manner, it also makes negative voltages positive.

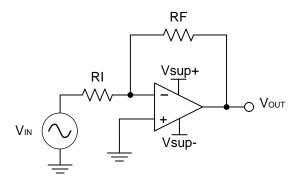


Figure 6. Inverting Amplifier

9.2.1 Design Requirements

The supply voltage must be chosen such that it is larger than the input voltage range and output range. For instance, this application scales a signal of ±0.5 V to ±1.8 V. Setting the supply at ±12 V is sufficient to accommodate this application.

9.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier:

$$A_{V} = \frac{VOUT}{VIN}$$

$$A_{V} = \frac{1.8}{-0.5} = -3.6$$
(2)

When the desired gain is determined, choose a value for RI or RF. Choosing a value in the $k\Omega$ range is desirable because the amplifier circuit uses currents in the milliamp range. This ensures the part does not draw too much current. For this example, choose 10 $k\Omega$ for RI which means 36 $k\Omega$ is used for R, as determined by Equation 3.

$$A_{V} = -\frac{RF}{RI} \tag{3}$$



Typical Application (continued)

9.2.3 Application Curve

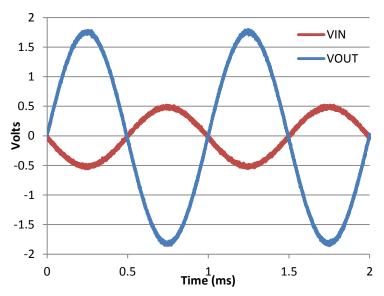


Figure 7. Input and Output Voltages of the Inverting Amplifier

10 Power Supply Recommendations

CAUTION

Supply voltages larger than 36 V for a single-supply or outside the range of ±18 V for a dual-supply can permanently damage the device (see Absolute Maximum Ratings).

Place the 0.1-µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see Layout Example.

Layout 11

11.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole, as well as the operational amplifier. Bypass capacitors are used to reduce the coupled noise by providing low impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1-uF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see the chapter extract, Circuit Board Layout Techniques (SLOA089).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keeping RF and RG close to the inverting

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Layout Guidelines (continued)

input minimizes parasitic capacitance, as shown in Layout Example.

- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

11.2 Layout Example

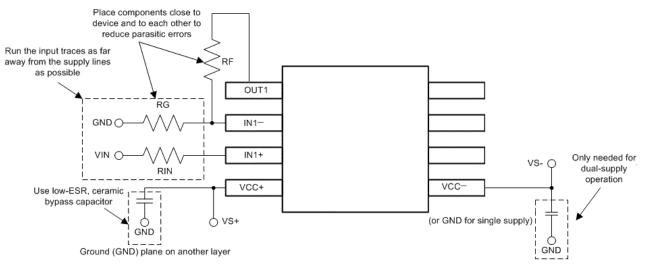


Figure 8. Operational Amplifier Board Layout for Noninverting Configuration

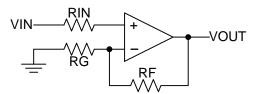


Figure 9. Operational Amplifier Schematic for Noninverting Configuration



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following Circuit Board Layout Techniques, SLOA089

12.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 1. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
LF347	Click here	Click here	Click here	Click here	Click here
LF347B	Click here	Click here	Click here	Click here	Click here

12.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
LF347BD	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF347B	Samples
LF347BDR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF347B	Samples
LF347BN	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	LF347BN	Samples
LF347D	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF347	Samples
LF347DG4	ACTIVE	SOIC	D	14	50	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF347	Samples
LF347DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF347	Samples
LF347DRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	LF347	Samples
LF347N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	LF347N	Samples
LF347NE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	0 to 70	LF347N	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



PACKAGE OPTION ADDENDUM

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(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

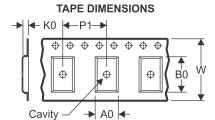
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TAPE AND REEL INFORMATION





A0	
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

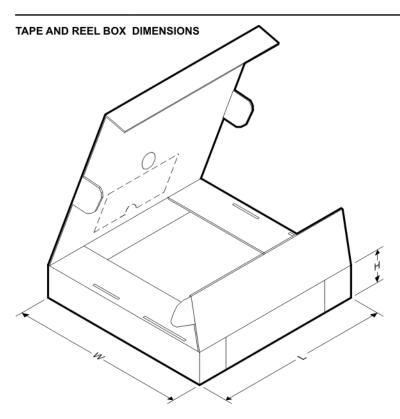
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

7 til diritoriolorio aro mominar												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LF347BDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
LF347DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LF347BDR	SOIC	D	14	2500	340.5	336.1	32.0
LF347DR	SOIC	D	14	2500	340.5	336.1	32.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
LF347BD	D	SOIC	14	50	507	8	3940	4.32
LF347BN	N	PDIP	14	25	506	13.97	11230	4.32
LF347D	D	SOIC	14	50	507	8	3940	4.32
LF347DG4	D	SOIC	14	50	507	8	3940	4.32
LF347N	N	PDIP	14	25	506	13.97	11230	4.32
LF347NE4	N	PDIP	14	25	506	13.97	11230	4.32

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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